

flowPIM 1 3rd gen
1200V / 25A
Features

- 3- rectifier, BRC, Inverter, NTC
- Very compact housing, easy to route
- IGBT2 phantom speed / EmCon4 technology
- Lower losses than IGBT3 or 4 for $f_{sw} > 8\text{kHz}$

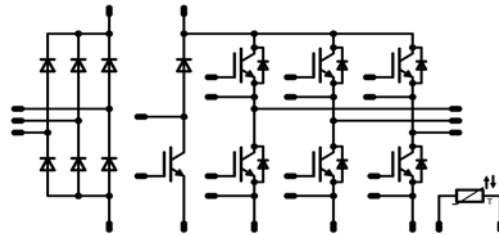
Target Applications

- Motor Drives with $8\text{kHz} < f_{sw} < 30\text{kHz}$
- Low audible noise applications ($f_{sw} > 16\text{kHz}$)
- High efficiency applications
- Centered aircon, fans, pumps

Types

- V23990-P589-A31-PM

flowPIM1 housing

Schematic


Maximum Ratings

 $T_j=25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Condition	Value	Unit
Input Rectifier Diode				
Peak repetitive reverse voltage	V_{RRM}		1600	V
DC forward current	I_{FAV}	$T_j=T_{jmax}$ $T_n=80^\circ\text{C}$	36	A
Surge forward current	I_{FSM}	$t_p=10\text{ms}$ $T_j=45^\circ\text{C}$	320	A
I^2t -value	I^2t		510	A^2s
Power dissipation per diode	P_{tot}	$T_j=T_{jmax}$ $T_n=80^\circ\text{C}$	40	W
Maximum junction temperature	T_{jmax}		150	$^\circ\text{C}$
Inverter Transistor				
Collector-emitter break down voltage	V_{CE}		1200	V
DC collector current	I_C	$T_j=T_{jmax}$ $T_n=80^\circ\text{C}$	27	A
Repetitive peak collector current	I_{Cpulse}	t_p limited by T_{jmax}	75	A
Power dissipation per IGBT	P_{tot}	$T_j=T_{jmax}$ $T_n=80^\circ\text{C}$	67	W
Gate-emitter peak voltage	V_{GE}		± 20	V
Maximum junction temperature	T_{jmax}		150	$^\circ\text{C}$

Maximum Ratings

 $T_j=25^{\circ}\text{C}$, unless otherwise specified

Parameter	Symbol	Condition	Value	Unit
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Inverter Diode

Peak repetitive reverse voltage	V_{RRM}		1200	V
DC forward current	I_F	$T_j=T_{jmax}$ $T_h=80^{\circ}\text{C}$	21	A
Repetitive peak forward current	I_{FRM}	t_p limited by T_{jmax}	50	A
Power dissipation per diode	P_{tot}	$T_j=T_{jmax}$ $T_h=80^{\circ}\text{C}$	37	W
Maximum junction temperature	T_{jmax}		175	$^{\circ}\text{C}$

Brc Transistor

Collector-emitter break down voltage	V_{CE}		1200	V
DC collector current	I_C	$T_j=T_{jmax}$ $T_h=80^{\circ}\text{C}$	15	A
Repetitive peak collector current	I_{Cpuls}	t_p limited by T_{jmax}	45	A
Power dissipation per IGBT	P_{tot}	$T_j=T_{jmax}$ $T_h=80^{\circ}\text{C}$	39	W
Gate-emitter peak voltage	V_{GE}		± 20	V
Short circuit ratings	t_{SC} V_{CC}	$T_j \leq 150^{\circ}\text{C}$ $V_{GE} = 15\text{V}$	10 800	μs V
Maximum junction temperature	T_{jmax}		175	$^{\circ}\text{C}$

Brc Diode

Peak repetitive reverse voltage	V_{RRM}		1200	V
DC forward current	I_F	$T_j=T_{jmax}$ $T_h=80^{\circ}\text{C}$	10	A
Repetitive peak forward current	I_{FRM}	t_p limited by T_{jmax}	20	A
Power dissipation per diode	P_{tot}	$T_j=T_{jmax}$ $T_h=80^{\circ}\text{C}$	21	W
Maximum junction temperature	T_{jmax}		175	$^{\circ}\text{C}$

Thermal Properties

Storage temperature	T_{stg}		-40...+125	$^{\circ}\text{C}$
Operation temperature under switching condition	T_{op}		-40...+($T_{jmax} - 25$)	$^{\circ}\text{C}$

Insulation Properties

Insulation voltage	V_{is}	$t=2\text{s}$ DC voltage	4000	V
Creepage distance			min 12.7	mm
Clearance			min 12.7	mm

Characteristic Values

Parameter	Symbol	Conditions					Value			Unit	
		$V_{GE}[V]$ or $V_{GS}[V]$	$V_r[V]$ or $V_{CE}[V]$ or $V_{DS}[V]$	$I_c[A]$ or $I_F[A]$ or $I_D[A]$	T_j	Min	Typ	Max			
Input Rectifier Diode											
Forward voltage	V_F				50	$T_j=25^\circ C$ $T_j=125^\circ C$	0.8	1.29 1.24	1.6	V	
Threshold voltage (for power loss calc. only)	V_{to}				50	$T_j=25^\circ C$ $T_j=125^\circ C$		0.93 0.82		V	
Slope resistance (for power loss calc. only)	r_t				50	$T_j=25^\circ C$ $T_j=125^\circ C$		7 9		m Ω	
Reverse current	I_r			1600		$T_j=25^\circ C$ $T_j=150^\circ C$			0.02 2	mA	
Thermal resistance chip to heatsink per chip	R_{thJH}	Thermal grease thickness $\leq 50\mu m$ $\lambda=0.61W/mK$						1.77		K/W	
Thermal resistance chip to case per chip	R_{thJC}							N/A			
Inverter Transistor											
Gate emitter threshold voltage	$V_{GE(th)}$	VCE=VGE			0.001	$T_j=25^\circ C$ $T_j=125^\circ C$	4.5	5.5	6.5	V	
Collector-emitter saturation voltage	$V_{CE(sat)}$		15		25	$T_j=25^\circ C$ $T_j=125^\circ C$	1.5	2.13 2.32	2.75	V	
Collector-emitter cut-off current incl. diode	I_{CES}		0	1200		$T_j=25^\circ C$ $T_j=125^\circ C$			0.01	mA	
Gate-emitter leakage current	I_{GES}		20	0		$T_j=25^\circ C$ $T_j=125^\circ C$			200	nA	
Integrated gate resistor	R_{gint}							-		Ω	
Turn-on delay time	$t_{d(on)}$	Rgoff=16 Ω Rgon=16 Ω	± 15	600	25	$T_j=25^\circ C$		136		ns	
Rise time	t_r					$T_j=125^\circ C$		137			
Turn-off delay time	$t_{d(off)}$					$T_j=25^\circ C$		13.2			
Fall time	t_f					$T_j=125^\circ C$		15.8			
Turn-on energy loss per pulse	E_{on}					$T_j=25^\circ C$		201			
Turn-off energy loss per pulse	E_{off}					$T_j=125^\circ C$		235			
Input capacitance	C_{ies}	f=1MHz	0	25		$T_j=25^\circ C$		2020		pF	
Output capacitance	C_{oss}								193		
Reverse transfer capacitance	C_{rss}								64		
Thermal resistance chip to heatsink per chip	R_{thJH}	Thermal grease thickness $\leq 50\mu m$ $\lambda=0.61W/mK$						1.05		K/W	
Thermal resistance chip to case per chip	R_{thJC}							N/A			
Inverter Diode											
Diode forward voltage	V_F				25	$T_j=25^\circ C$ $T_j=150^\circ C$	1.3	1.9 1.89	2.2	V	
Peak reverse recovery current	I_{RRM}					$T_j=25^\circ C$ $T_j=125^\circ C$		60 65		A	
Reverse recovery time	t_{rr}	Rgoff=16 Ω	± 15	600	25	$T_j=25^\circ C$		84		ns	
Reverse recovered charge	Q_{rr}					$T_j=125^\circ C$		153			
Peak rate of fall of recovery current	$di(rec)max/dt$					$T_j=25^\circ C$		2.68			
Reverse recovered energy	Erec					$T_j=125^\circ C$		4.64			
Thermal resistance chip to heatsink per chip	R_{thJH}	Thermal grease thickness $\leq 50\mu m$ $\lambda=0.61W/mK$						1.92		K/W	
Thermal resistance chip to case per chip	R_{thJC}							N/A			

Characteristic Values

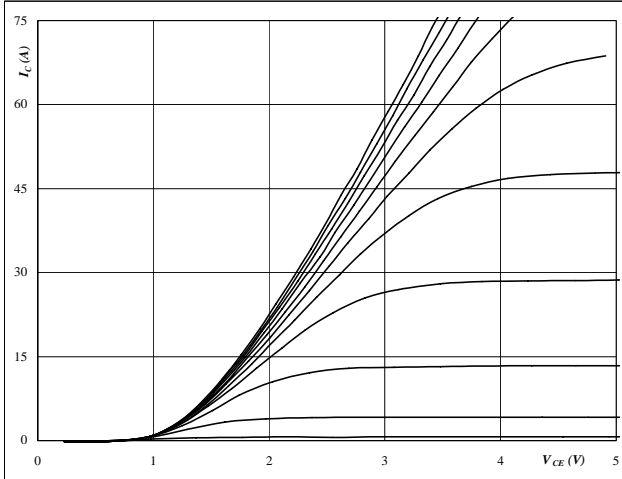
Parameter	Symbol	Conditions					Value			Unit
		$V_{GE}[V]$ or $V_{GS}[V]$	$V_r[V]$ or $V_{CE}[V]$ or $V_{DS}[V]$	$I_c[A]$ or $I_F[A]$ or $I_D[A]$	T_j	Min	Typ	Max		
Brc Transistor										
Gate emitter threshold voltage	$V_{GE(th)}$	VCE=VGE			0.0005	$T_j=25^\circ C$ $T_j=150^\circ C$	5	5.8	6.5	V
Collector-emitter saturation voltage	$V_{CE(sat)}$		15		15	$T_j=25^\circ C$ $T_j=150^\circ C$	1.6	1.88 2.30	2.2	V
Collector-emitter cut-off incl. diode	I_{CES}		0	1200		$T_j=25^\circ C$ $T_j=150^\circ C$			0.005	mA
Gate-emitter leakage current	I_{GES}		20	0		$T_j=25^\circ C$ $T_j=150^\circ C$			200	nA
Integrated gate resistor	R_{gint}							-		Ω
Turn-on delay time	$t_{d(on)}$	Rgon=32 Ω Rgoff=32 Ω	± 15	600	15	$T_j=25^\circ C$		87		ns
Rise time	t_r					$T_j=125^\circ C$		87		
Turn-off delay time	$t_{d(off)}$					$T_j=25^\circ C$		24		
Fall time	t_f					$T_j=125^\circ C$		28		
Turn-on energy loss per pulse	E_{on}					$T_j=25^\circ C$		194		
Turn-off energy loss per pulse	E_{off}	$T_j=125^\circ C$		256						
Input capacitance	C_{ies}	f=1MHz	0	25		$T_j=25^\circ C$		900		pF
Output capacitance	C_{oss}					$T_j=25^\circ C$		80		
Reverse transfer capacitance	C_{rss}					$T_j=25^\circ C$		55		
Gate charge	Q_{Gate}	Vcc=960V	± 15		15	$T_j=25^\circ C$		120		nC
Thermal resistance chip to heatsink per chip	R_{thJH}	Thermal grease thickness $\leq 50\mu m$						1.8		K/W
Thermal resistance chip to case per chip	R_{thJC}	$\lambda=0.61W/mK$						N/A		
Brc Diode										
Diode forward voltage	V_F				10	$T_j=25^\circ C$ $T_j=150^\circ C$	1.3	1.85 1.76	2.2	V
Reverse leakage current	I_r		± 15	600	10	$T_j=25^\circ C$ $T_j=150^\circ C$			5	μA
Peak reverse recovery current	I_{RRM}	Rgon=32 Ω	± 15	600	10	$T_j=25^\circ C$		10		A
Reverse recovery time	t_{rr}					$T_j=125^\circ C$		12		
Reverse recovered charge	Q_{rr}					$T_j=25^\circ C$		324		
Peak rate of fall of recovery current	$di(rec)max/dt$					$T_j=125^\circ C$		489		
Reverse recovery energy	E_{rec}					$T_j=25^\circ C$		1.38		
Thermal resistance chip to heatsink per chip	R_{thJH}	Thermal grease thickness $\leq 50\mu m$						3.28		K/W
Thermal resistance chip to case per chip	R_{thJC}	$\lambda=0.61W/mK$						N/A		
Thermistor										
Rated resistance	R					$T_j=25^\circ C$ $T_j=125^\circ C$	20.9	22 0.75	23.1	k Ω
Operating current	I					$T_j=25^\circ C$			0.3	mA
Power dissipation	P					$T_j=25^\circ C$		200		mW
B-value	$B_{(25/50)}$	Tol. $\pm 3\%$				$T_j=25^\circ C$		3950		K

Output Inverter

Figure 1 Output inverter IGBT

Typical output characteristics

$$I_C = f(V_{CE})$$

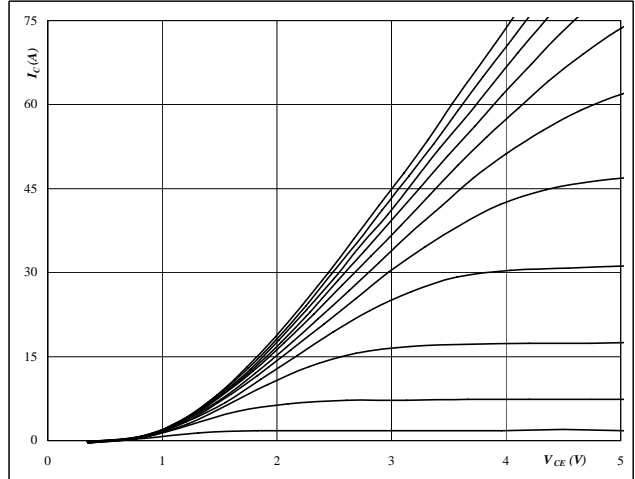


At
 $t_p = 250 \mu s$
 $T_j = 25 \text{ } ^\circ C$
 V_{GE} from 7 V to 17 V in steps of 1 V

Figure 2 Output inverter IGBT

Typical output characteristics

$$I_C = f(V_{CE})$$

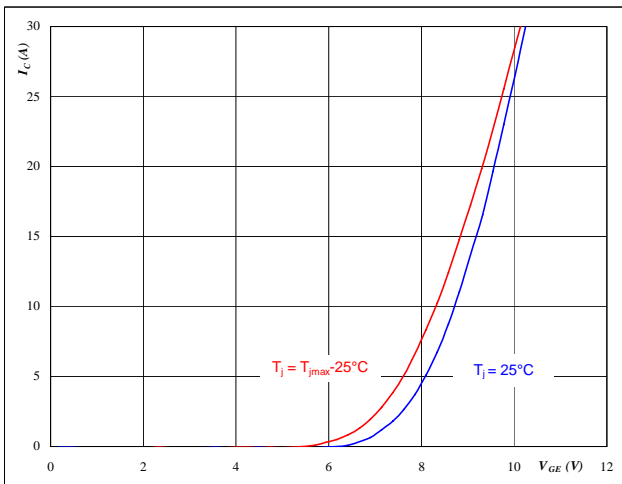


At
 $t_p = 250 \mu s$
 $T_j = 125 \text{ } ^\circ C$
 V_{GE} from 7 V to 17 V in steps of 1 V

Figure 3 Output inverter IGBT

Typical transfer characteristics

$$I_C = f(V_{GE})$$

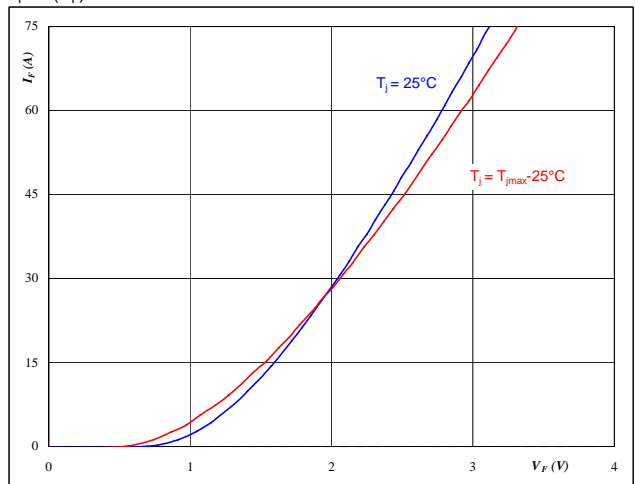


At
 $t_p = 250 \mu s$
 $V_{CE} = 10 V$

Figure 4 Output inverter FRED

Typical diode forward current as a function of forward voltage

$$I_F = f(V_F)$$

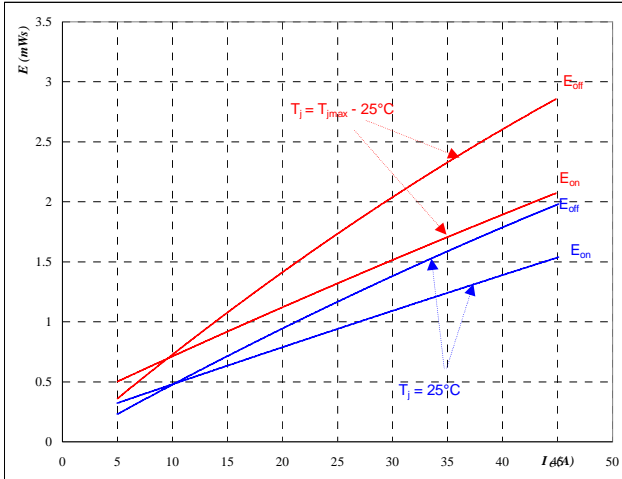


At
 $t_p = 250 \mu s$

Output Inverter

Figure 5 Output inverter IGBT

Typical switching energy losses
as a function of collector current
 $E = f(I_C)$

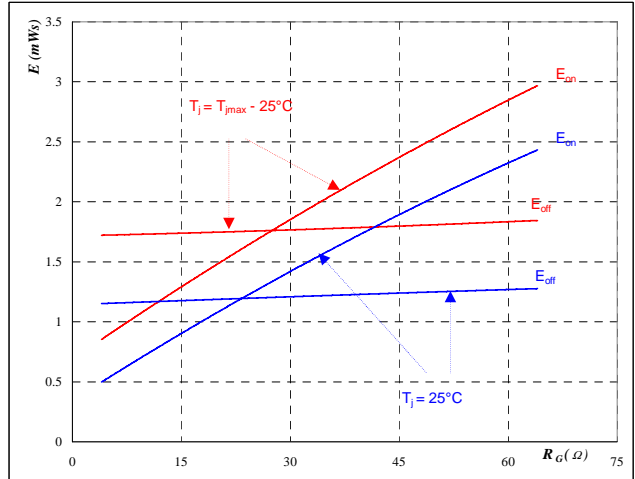


With an inductive load at

$T_J =$	25/125	°C
$V_{CE} =$	600	V
$V_{GE} =$	±15	V
$R_{gon} =$	16	Ω
$R_{goff} =$	16	Ω

Figure 6 Output inverter IGBT

Typical switching energy losses
as a function of gate resistor
 $E = f(R_G)$

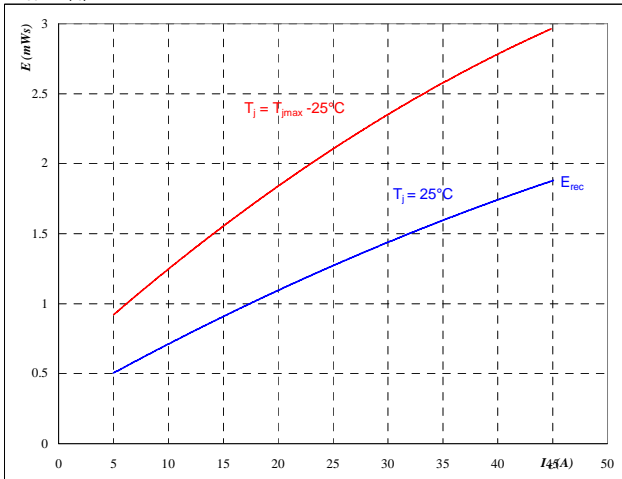


With an inductive load at

$T_J =$	25/125	°C
$V_{CE} =$	600	V
$V_{GE} =$	±15	V
$I_C =$	25	A

Figure 7 Output inverter IGBT

Typical reverse recovery energy loss
as a function of collector current
 $E_{rec} = f(I_C)$

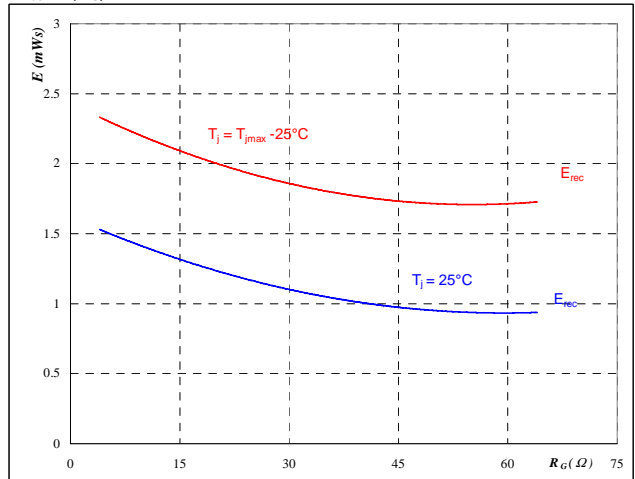


With an inductive load at

$T_J =$	25/125	°C
$V_{CE} =$	600	V
$V_{GE} =$	±15	V
$R_{gon} =$	16	Ω

Figure 8 Output inverter IGBT

Typical reverse recovery energy loss
as a function of gate resistor
 $E_{rec} = f(R_G)$



With an inductive load at

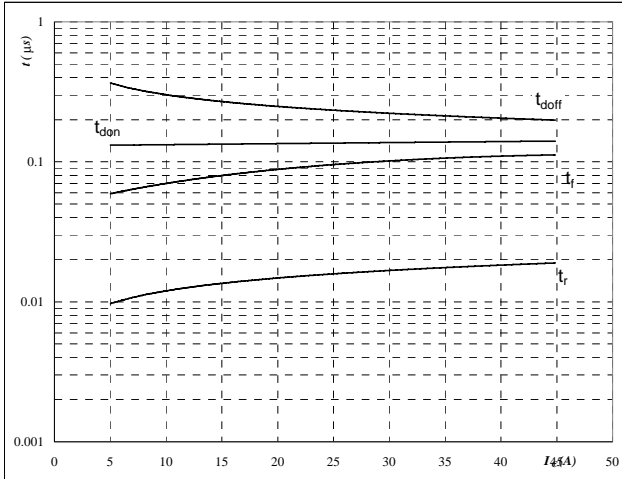
$T_J =$	25/125	°C
$V_{CE} =$	600	V
$V_{GE} =$	±15	V
$I_C =$	25	A

Output Inverter

Figure 9 Output inverter IGBT

Typical switching times as a function of collector current

$t = f(I_C)$



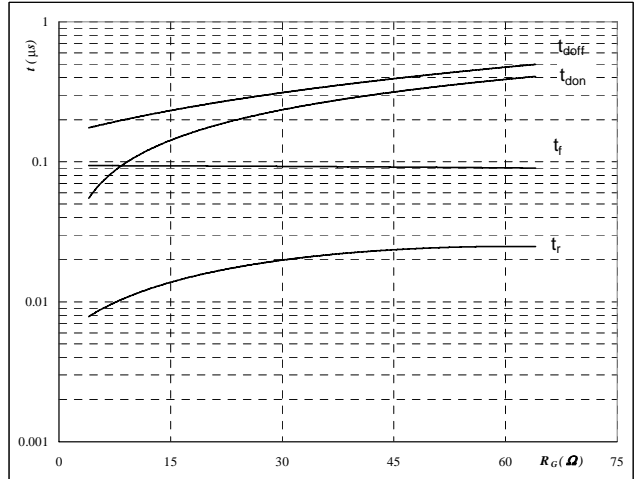
With an inductive load at

$T_J =$	125	°C
$V_{CE} =$	600	V
$V_{GE} =$	±15	V
$R_{gon} =$	16	Ω
$R_{goff} =$	16	Ω

Figure 10 Output inverter IGBT

Typical switching times as a function of gate resistor

$t = f(R_G)$



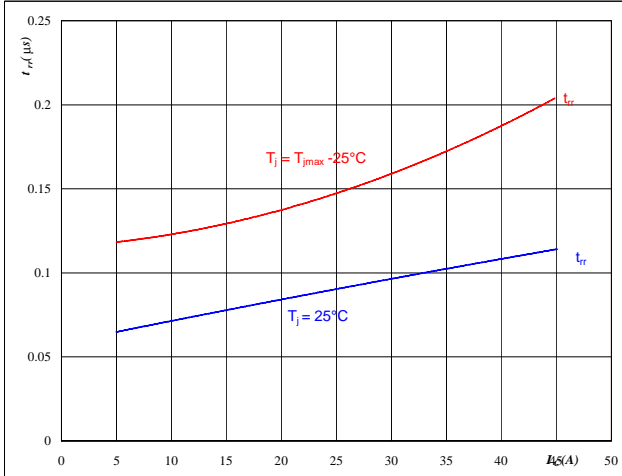
With an inductive load at

$T_J =$	125	°C
$V_{CE} =$	600	V
$V_{GE} =$	±15	V
$I_C =$	25	A

Figure 11 Output inverter FRED

Typical reverse recovery time as a function of collector current

$t_{rr} = f(I_C)$



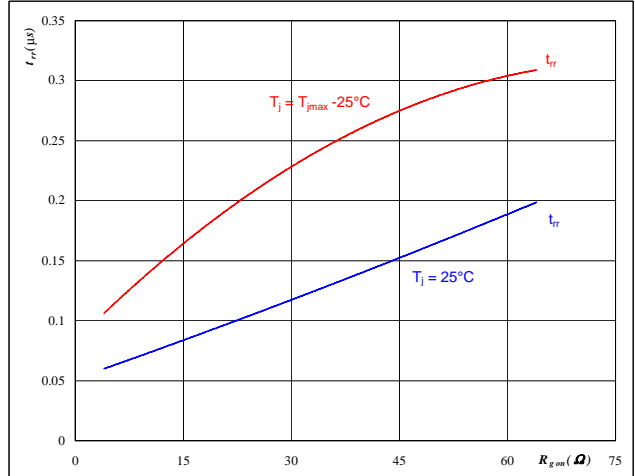
At

$T_J =$	25/125	°C
$V_{CE} =$	600	V
$V_{GE} =$	±15	V
$R_{gon} =$	16	Ω

Figure 12 Output inverter FRED

Typical reverse recovery time as a function of IGBT turn on gate resistor

$t_{rr} = f(R_{gon})$



At

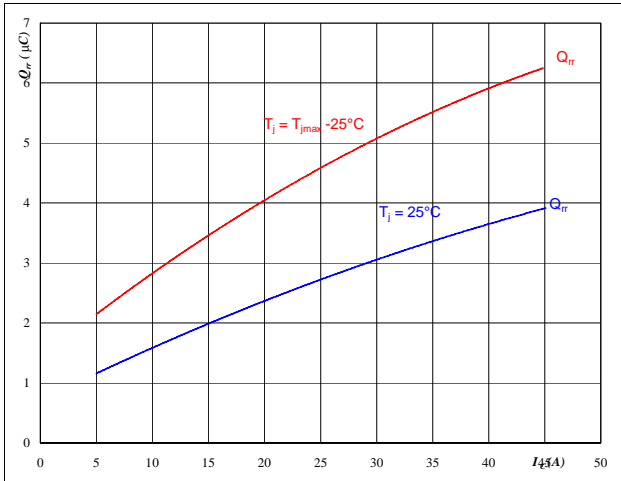
$T_J =$	25/125	°C
$V_R =$	600	V
$I_F =$	25	A
$V_{GE} =$	±15	V

Output Inverter

Figure 13 Output inverter FRED

Typical reverse recovery charge as a function of collector current

$$Q_{rr} = f(I_C)$$

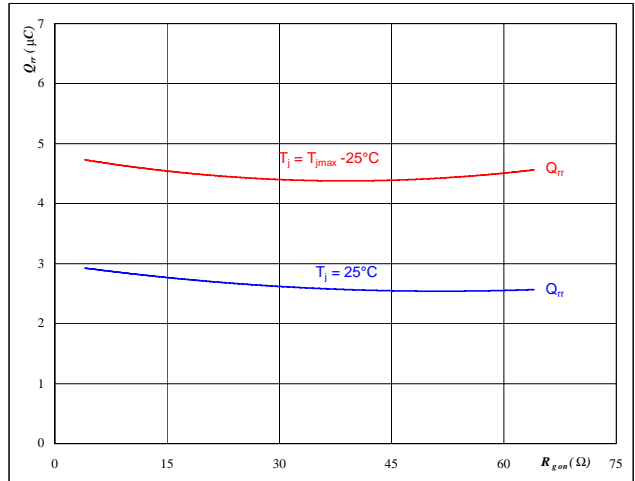


At
 $T_j = 25/125$ °C
 $V_{CE} = 600$ V
 $V_{GE} = \pm 15$ V
 $R_{gon} = 16$ Ω

Figure 14 Output inverter FRED

Typical reverse recovery charge as a function of IGBT turn on gate resistor

$$Q_{rr} = f(R_{gon})$$

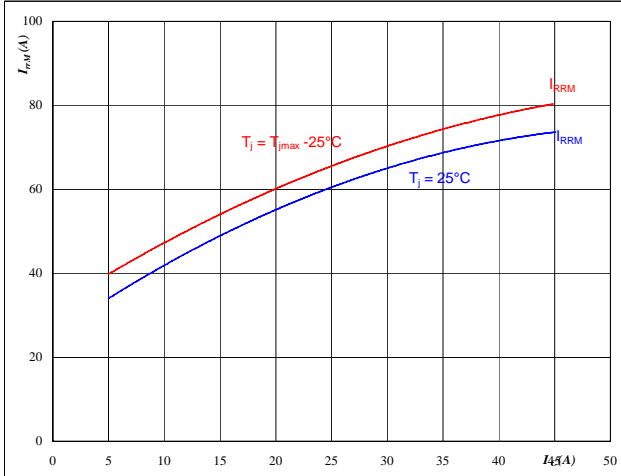


At
 $T_j = 25/125$ °C
 $V_R = 600$ V
 $I_F = 25$ A
 $V_{GE} = \pm 15$ V

Figure 15 Output inverter FRED

Typical reverse recovery current as a function of collector current

$$I_{RRM} = f(I_C)$$

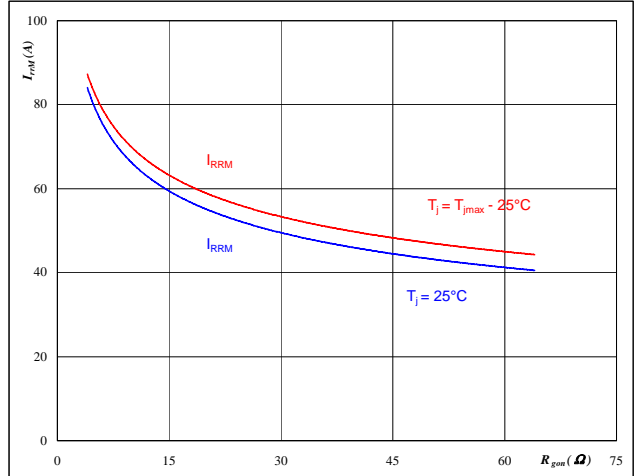


At
 $T_j = 25/125$ °C
 $V_{CE} = 600$ V
 $V_{GE} = \pm 15$ V
 $R_{gon} = 16$ Ω

Figure 16 Output inverter FRED

Typical reverse recovery current as a function of IGBT turn on gate resistor

$$I_{RRM} = f(R_{gon})$$



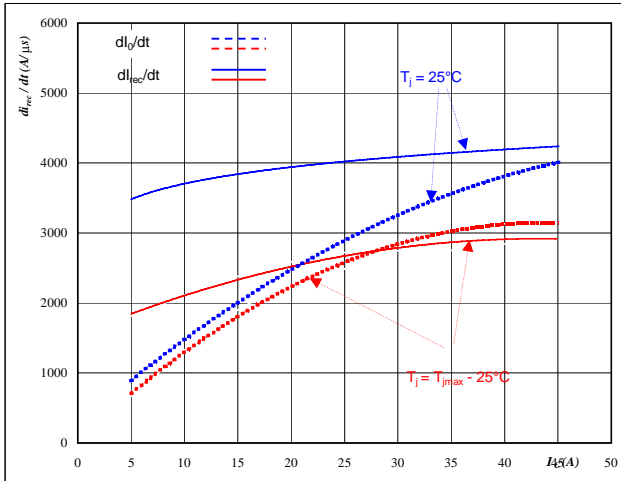
At
 $T_j = 25/125$ °C
 $V_R = 600$ V
 $I_F = 25$ A
 $V_{GE} = \pm 15$ V

Output Inverter

Figure 17 Output inverter FRED

Typical rate of fall of forward and reverse recovery current as a function of collector current

$$dI_f/dt, dI_{rec}/dt = f(I_c)$$

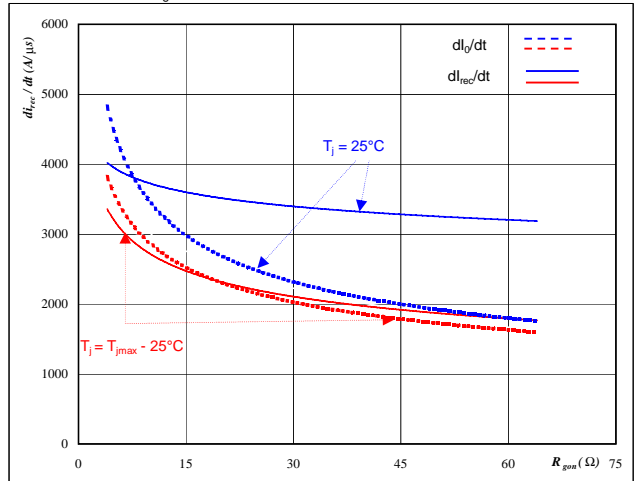


At
 $T_j = 25/125 \text{ } ^\circ\text{C}$
 $V_{CE} = 600 \text{ V}$
 $V_{GE} = \pm 15 \text{ V}$
 $R_{gon} = 16 \text{ } \Omega$

Figure 18 Output inverter FRED

Typical rate of fall of forward and reverse recovery current as a function of IGBT turn on gate resistor

$$dI_f/dt, dI_{rec}/dt = f(R_{gon})$$

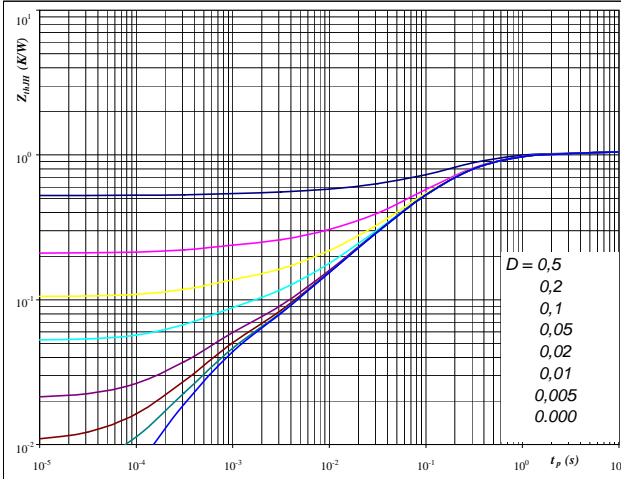


At
 $T_j = 25/125 \text{ } ^\circ\text{C}$
 $V_R = 600 \text{ V}$
 $I_F = 25 \text{ A}$
 $V_{GE} = \pm 15 \text{ V}$

Figure 19 Output inverter IGBT

IGBT transient thermal impedance as a function of pulse width

$$Z_{thJH} = f(t_p)$$



At
 $D = t_p / T$
 $R_{thJH} = 1.05 \text{ K/W}$ (Single device heated)
 $R_{thJH} = 1.05 \text{ K/W}$ (All devices heated)

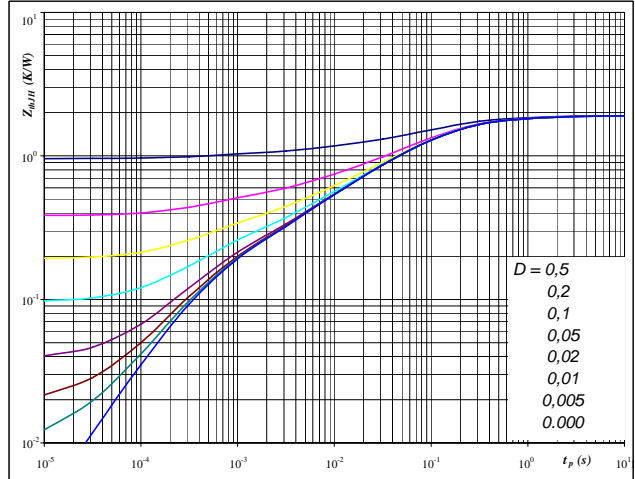
IGBT thermal model values

R (C/W)	Tau (s)	R (C/W)
0.09	2.6E+00	0.09
0.42	3.2E-01	0.42
0.41	8.5E-02	0.41
0.09	1.0E-02	0.09
0.04	6.4E-04	0.04

Figure 20 Output inverter FRED

FRED transient thermal impedance as a function of pulse width

$$Z_{thJH} = f(t_p)$$



At
 $D = t_p / T$
 $R_{thJH} = 1.92 \text{ K/W}$ (Single device heated)
 $R_{thJH} = 1.92 \text{ K/W}$ (All devices heated)

FRED thermal model values

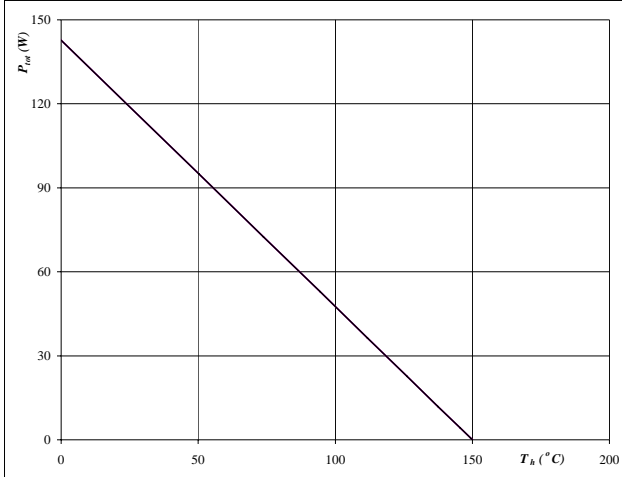
R (C/W)	Tau (s)	R (C/W)
0.04	9.5E+00	0.04
0.21	7.9E-01	0.21
0.80	1.3E-01	0.80
0.51	2.8E-02	0.51
0.21	4.1E-03	0.21
0.14	4.5E-04	0.14

Output Inverter

Figure 21 Output inverter IGBT

Power dissipation as a function of heatsink temperature

$$P_{tot} = f(T_h)$$

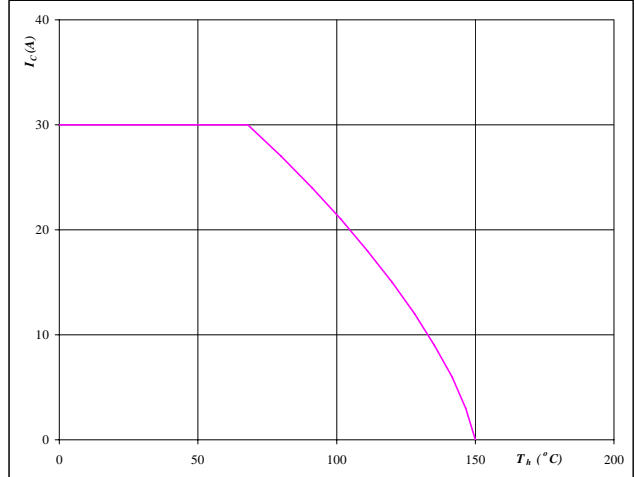


At $T_j = 150$ °C
— single heating
— overall heating

Figure 22 Output inverter IGBT

Collector current as a function of heatsink temperature

$$I_C = f(T_h)$$

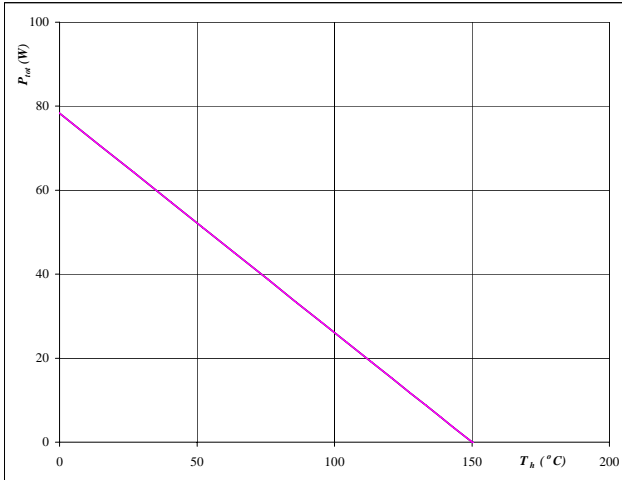


At $T_j = 150$ °C
 $V_{GE} = 15$ V

Figure 23 Output inverter FRED

Power dissipation as a function of heatsink temperature

$$P_{tot} = f(T_h)$$

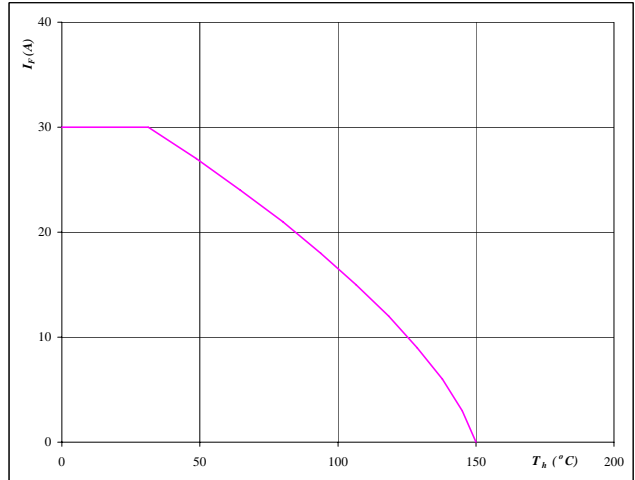


At $T_j = 150$ °C
— single heating
— overall heating

Figure 24 Output inverter FRED

Forward current as a function of heatsink temperature

$$I_F = f(T_h)$$



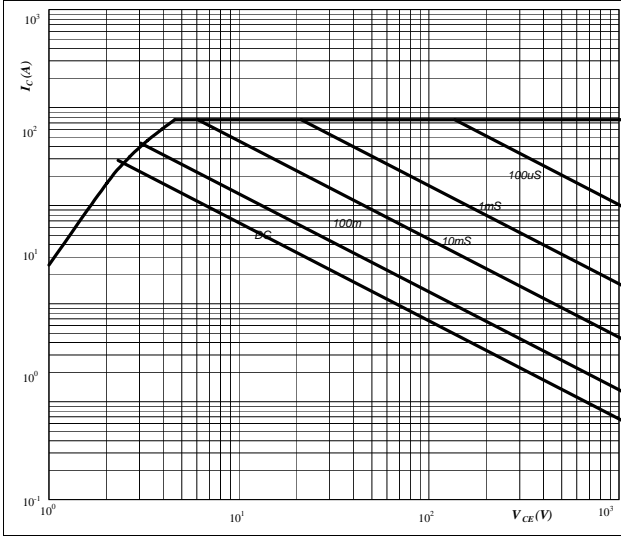
At $T_j = 150$ °C

Output Inverter

Figure 25 Output inverter IGBT

Safe operating area as a function
of collector-emitter voltage

$$I_C = f(V_{CE})$$



At

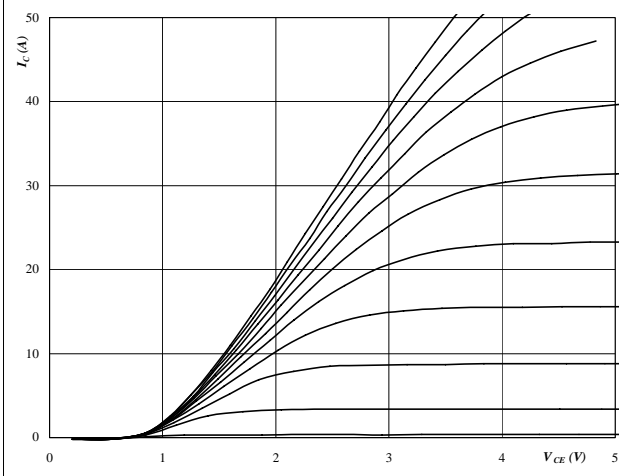
D = single pulse
 Th = 80 °C
 V_{GE} = ±15 V
 T_j = T_{jmax} °C

Brake

Figure 1 Brake IGBT

Typical output characteristics

$$I_C = f(V_{CE})$$

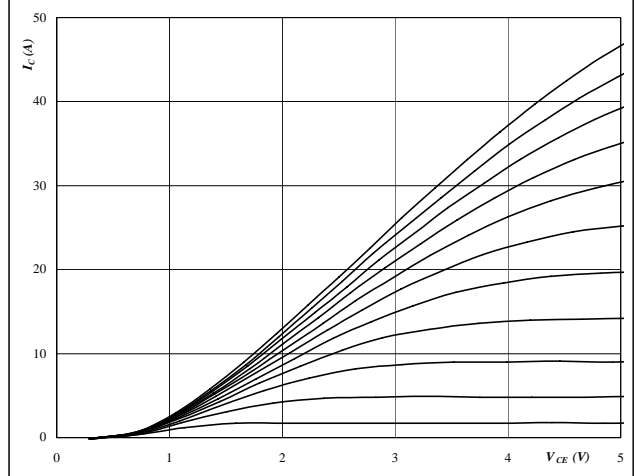


At
 $t_p = 250 \mu s$
 $T_j = 25 \text{ }^\circ C$
 V_{GE} from 7 V to 17 V in steps of 1 V

Figure 2 Brake IGBT

Typical output characteristics

$$I_C = f(V_{CE})$$

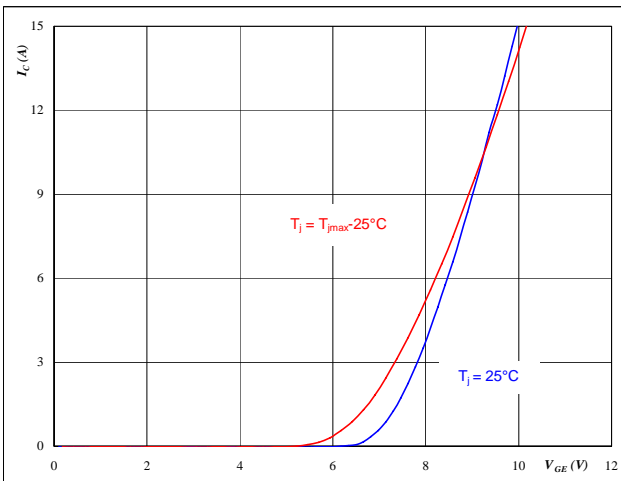


At
 $t_p = 250 \mu s$
 $T_j = 125 \text{ }^\circ C$
 V_{GE} from 7 V to 17 V in steps of 1 V

Figure 3 Brake IGBT

Typical transfer characteristics

$$I_C = f(V_{GE})$$

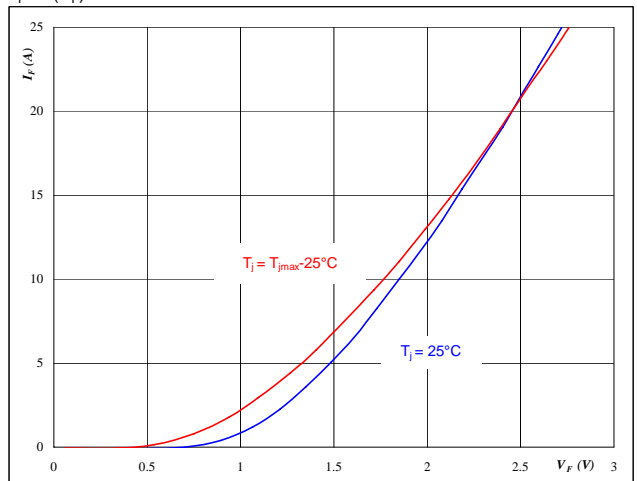


At
 $t_p = 250 \mu s$
 $V_{CE} = 10 V$

Figure 4 Brake FRED

Typical diode forward current as a function of forward voltage

$$I_F = f(V_F)$$

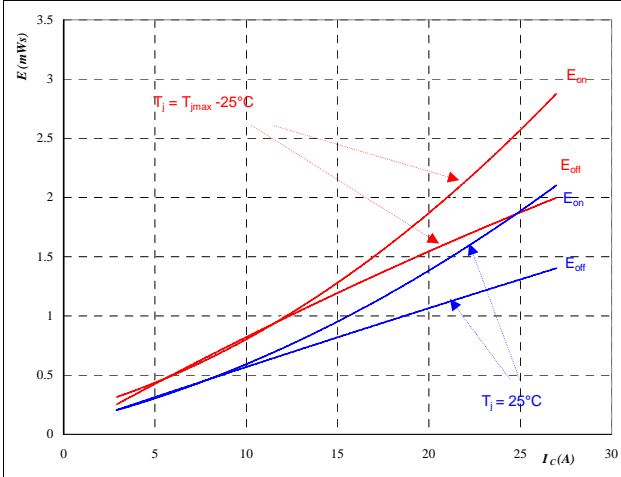


At
 $t_p = 250 \mu s$

Brake

Figure 5 Brake IGBT

Typical switching energy losses
as a function of collector current
 $E = f(I_C)$

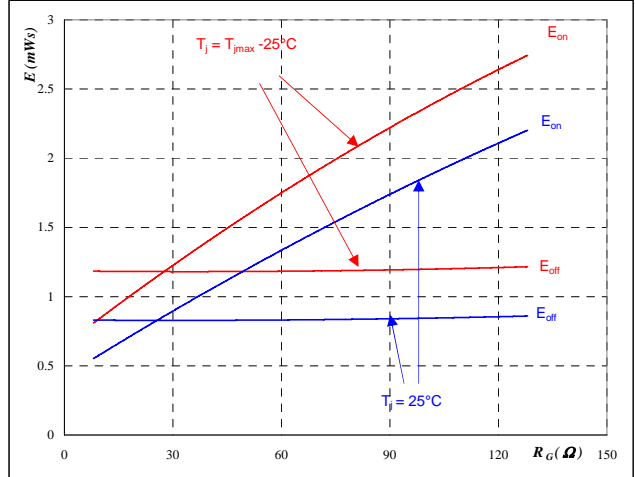


With an inductive load at

$T_j =$	25/125	°C
$V_{CE} =$	600	V
$V_{GE} =$	±15	V
$R_{gon} =$	32	Ω
$R_{goff} =$	32	Ω

Figure 6 Brake IGBT

Typical switching energy losses
as a function of gate resistor
 $E = f(R_G)$

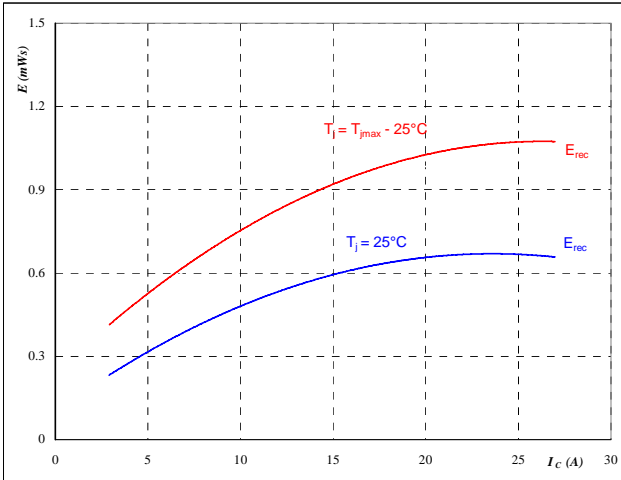


With an inductive load at

$T_j =$	25/125	°C
$V_{CE} =$	600	V
$V_{GE} =$	±15	V
$I_C =$	15	A

Figure 7 Brake IGBT

Typical reverse recovery energy loss
as a function of collector current
 $E_{rec} = f(I_C)$

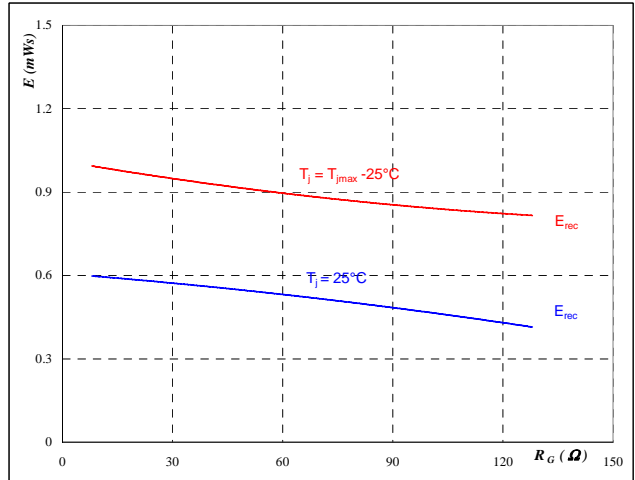


With an inductive load at

$T_j =$	25/125	°C
$V_{CE} =$	600	V
$V_{GE} =$	±15	V
$R_{gon} =$	32	Ω

Figure 8 Brake IGBT

Typical reverse recovery energy loss
as a function of gate resistor
 $E_{rec} = f(R_G)$



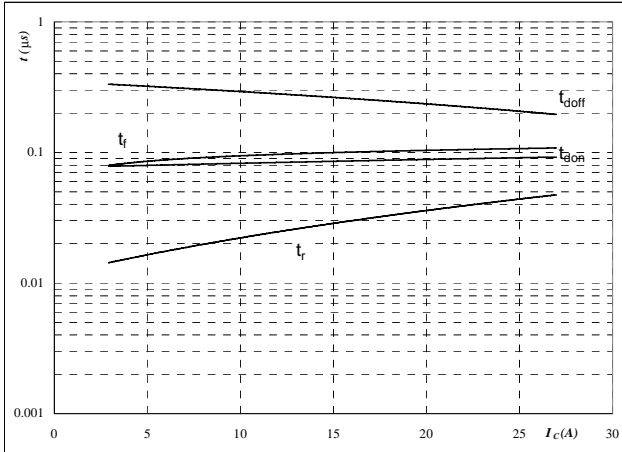
With an inductive load at

$T_j =$	25/125	°C
$V_{CE} =$	600	V
$V_{GE} =$	±15	V
$I_C =$	15	A

Brake

Figure 9 Brake IGBT

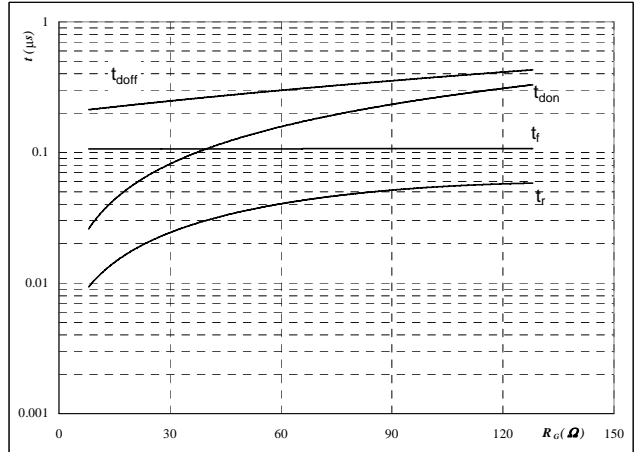
Typical switching times as a function of collector current
 $t = f(I_C)$



With an inductive load at
 $T_j = 25/125 \text{ } ^\circ\text{C}$
 $V_{CE} = 600 \text{ V}$
 $V_{GE} = \pm 15 \text{ V}$
 $R_{gon} = 32 \text{ } \Omega$
 $R_{goff} = 32 \text{ } \Omega$

Figure 10 Brake IGBT

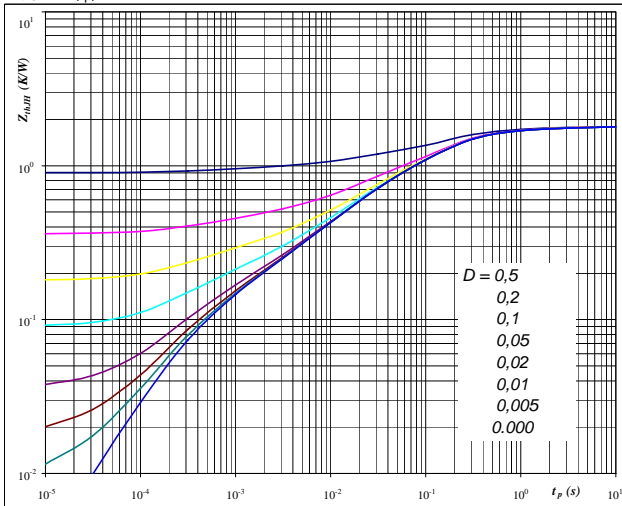
Typical switching times as a function of gate resistor
 $t = f(R_G)$



With an inductive load at
 $T_j = 25/125 \text{ } ^\circ\text{C}$
 $V_{CE} = 600 \text{ V}$
 $V_{GE} = \pm 15 \text{ V}$
 $I_C = 15 \text{ A}$

Figure 11 Brake IGBT

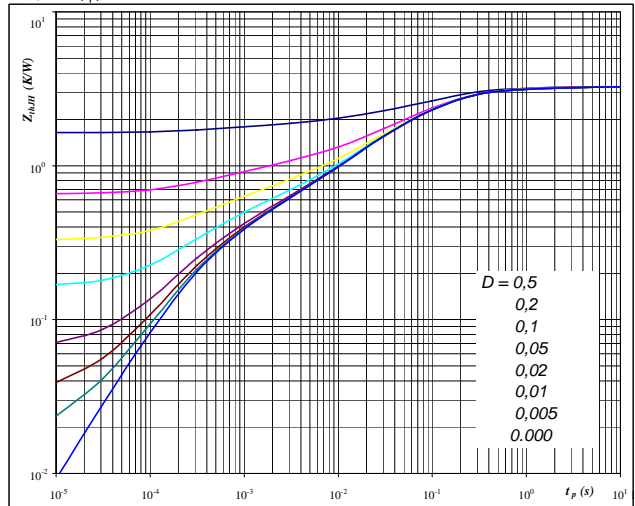
IGBT transient thermal impedance as a function of pulse width
 $Z_{thJH} = f(t_p)$



At
 $D = t_p / T$
 $R_{thJH} = 1.80 \text{ K/W}$

Figure 12 Brake FRED

FRED transient thermal impedance as a function of pulse width
 $Z_{thJH} = f(t_p)$



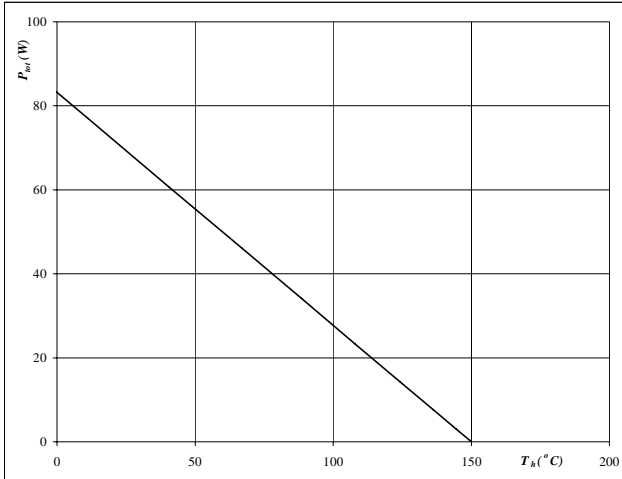
At
 $D = t_p / T$
 $R_{thJH} = 3.28 \text{ K/W}$

Brake

Figure 13 Brake IGBT

Power dissipation as a function of heatsink temperature

$$P_{tot} = f(T_h)$$

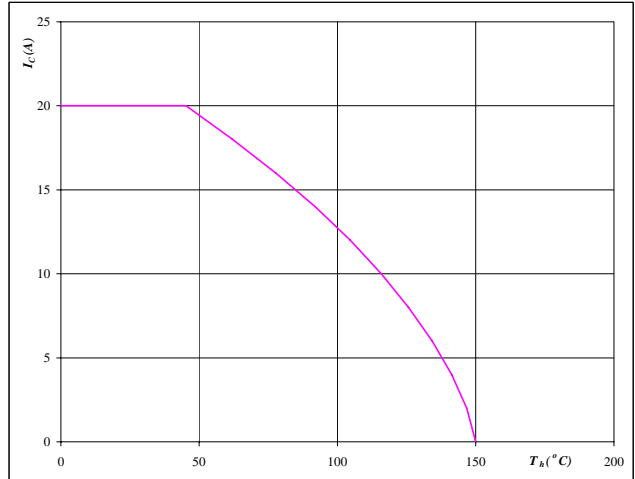


At
 $T_j = 150$ °C

Figure 14 Brake IGBT

Collector current as a function of heatsink temperature

$$I_C = f(T_h)$$

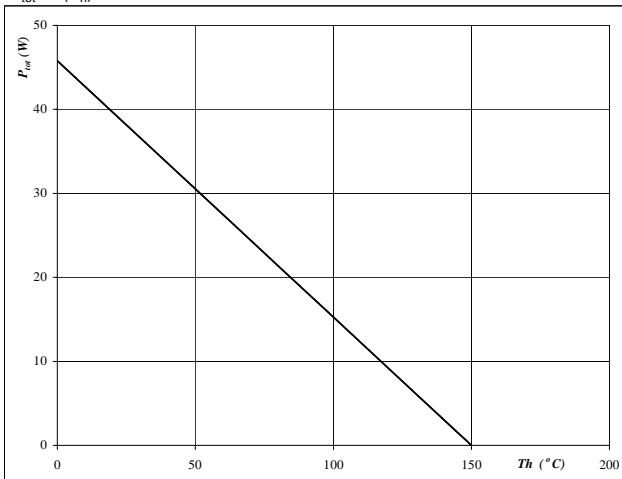


At
 $T_j = 150$ °C
 $V_{GE} = 15$ V

Figure 15 Brake FRED

Power dissipation as a function of heatsink temperature

$$P_{tot} = f(T_h)$$

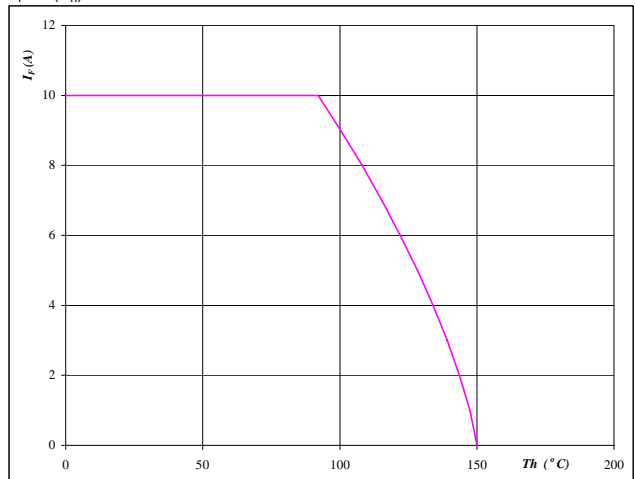


At
 $T_j = 150$ °C

Figure 16 Brake FRED

Forward current as a function of heatsink temperature

$$I_F = f(T_h)$$



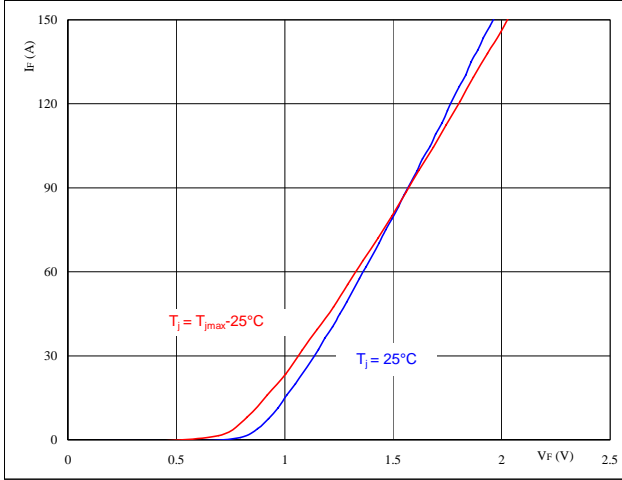
At
 $T_j = 150$ °C

Input Rectifier Bridge

Figure 1 Rectifier diode

Typical diode forward current as a function of forward voltage

$I_F = f(V_F)$

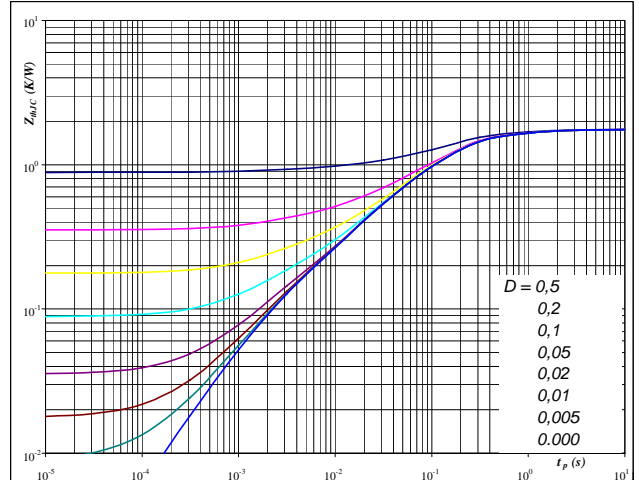


At
 $t_p = 250 \mu s$

Figure 2 Rectifier diode

Diode transient thermal impedance as a function of pulse width

$Z_{thJH} = f(t_p)$

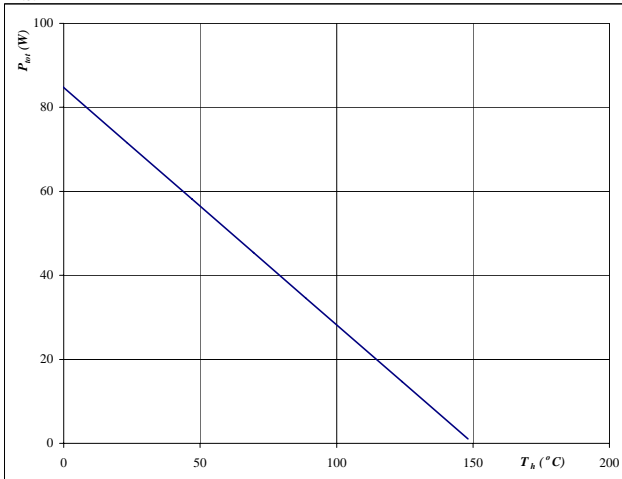


At
 $D = t_p / T$
 $R_{thJH} = 1.770 \text{ K/W}$

Figure 3 Rectifier diode

Power dissipation as a function of heatsink temperature

$P_{tot} = f(T_h)$

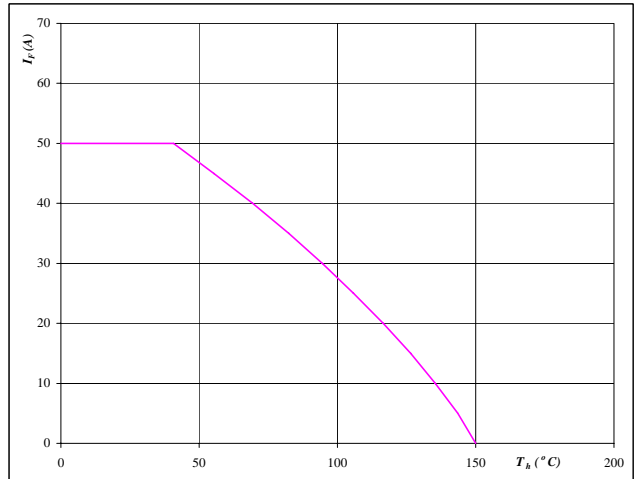


At
 $T_j = 150 \text{ °C}$

Figure 4 Rectifier diode

Forward current as a function of heatsink temperature

$I_F = f(T_h)$



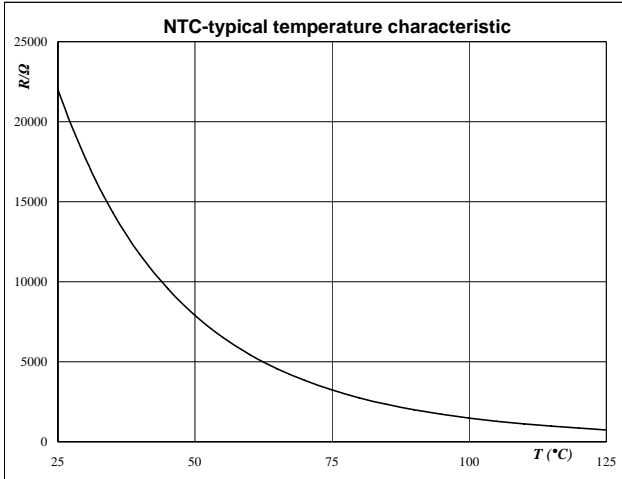
At
 $T_j = 150 \text{ °C}$

Thermistor

Figure 1 Thermistor

Typical NTC characteristic
as a function of temperature

$$R_T = f(T)$$



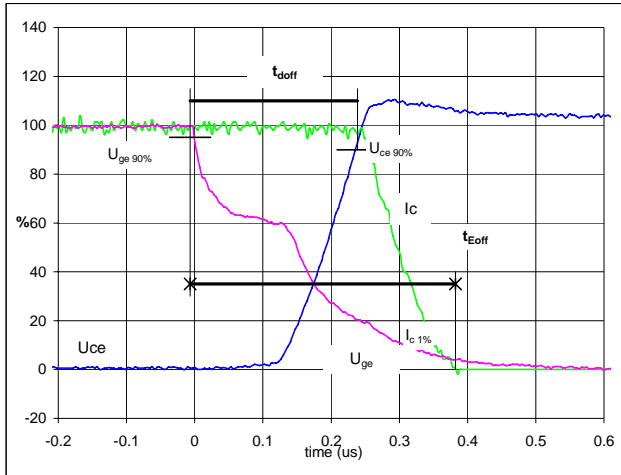
Switching Definitions Output Inverter

General conditions

T_j	=	125 °C
R_{gon}	=	16 Ω
R_{goff}	=	16 Ω

Figure 1 Output inverter IGBT

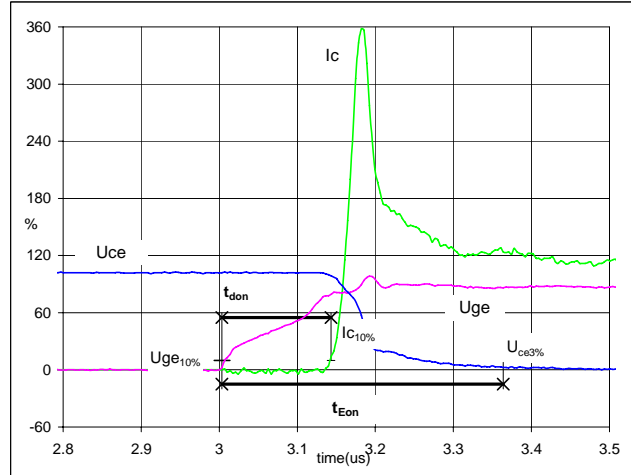
Turn-off Switching Waveforms & definition of t_{doff} , t_{Eoff}
(t_{Eoff} = integrating time for E_{off})



V_{GE} (0%) =	-15	V
V_{GE} (100%) =	15	V
V_C (100%) =	600	V
I_C (100%) =	25	A
t_{doff} =	0.24	μ s
t_{Eoff} =	0.39	μ s

Figure 2 Output inverter IGBT

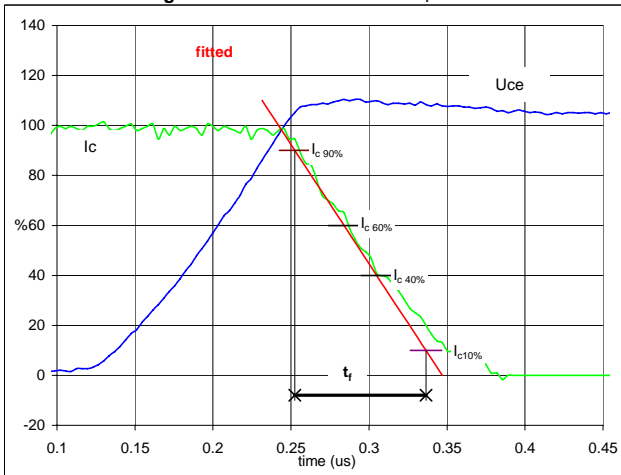
Turn-on Switching Waveforms & definition of t_{don} , t_{Eon}
(t_{Eon} = integrating time for E_{on})



V_{GE} (0%) =	-15	V
V_{GE} (100%) =	15	V
V_C (100%) =	600	V
I_C (100%) =	25	A
t_{don} =	0.14	μ s
t_{Eon} =	0.36	μ s

Figure 3 Output inverter IGBT

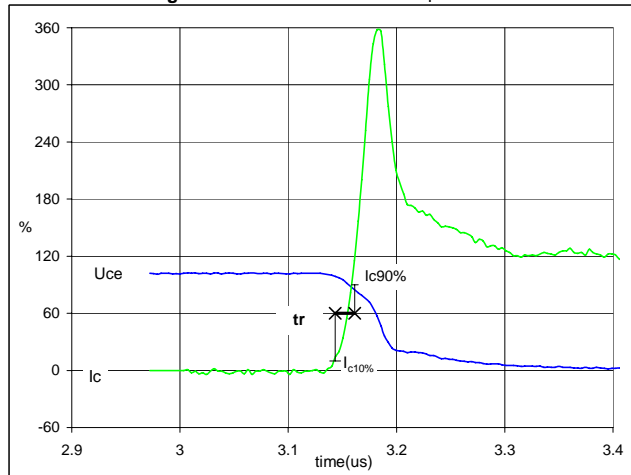
Turn-off Switching Waveforms & definition of t_f



V_C (100%) =	600	V
I_C (100%) =	25	A
t_f =	0.10	μ s

Figure 4 Output inverter IGBT

Turn-on Switching Waveforms & definition of t_r

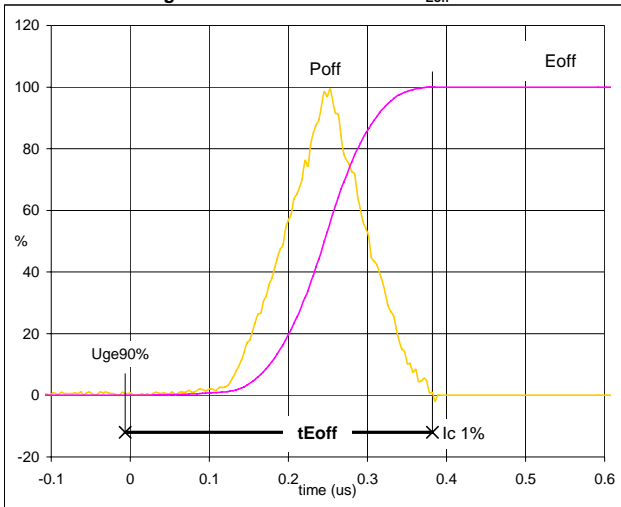


V_C (100%) =	600	V
I_C (100%) =	25	A
t_r =	0.02	μ s

Switching Definitions Output Inverter

Figure 5 Output inverter IGBT

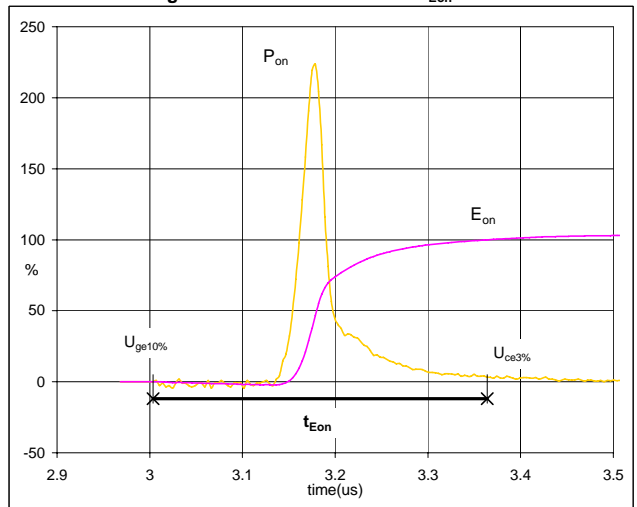
Turn-off Switching Waveforms & definition of t_{Eoff}



$P_{off}(100\%) = 14.95$ kW
 $E_{off}(100\%) = 1.74$ mJ
 $t_{Eoff} = 0.39$ μ s

Figure 6 Output inverter IGBT

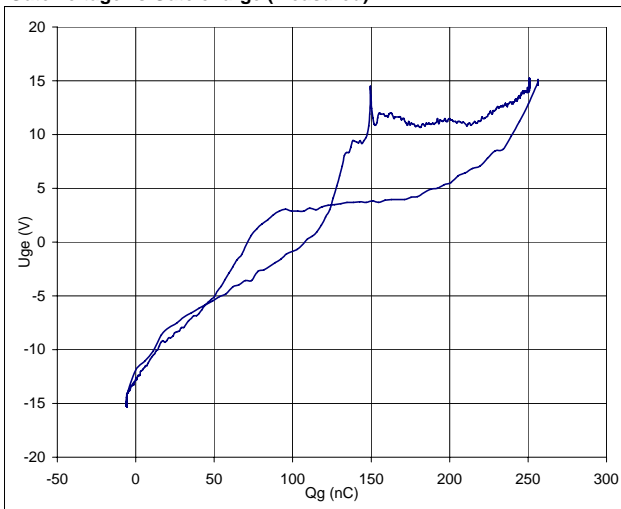
Turn-on Switching Waveforms & definition of t_{Eon}



$P_{on}(100\%) = 14.95$ kW
 $E_{on}(100\%) = 1.32$ mJ
 $t_{Eon} = 0.36$ μ s

Figure 7 Output inverter FRED

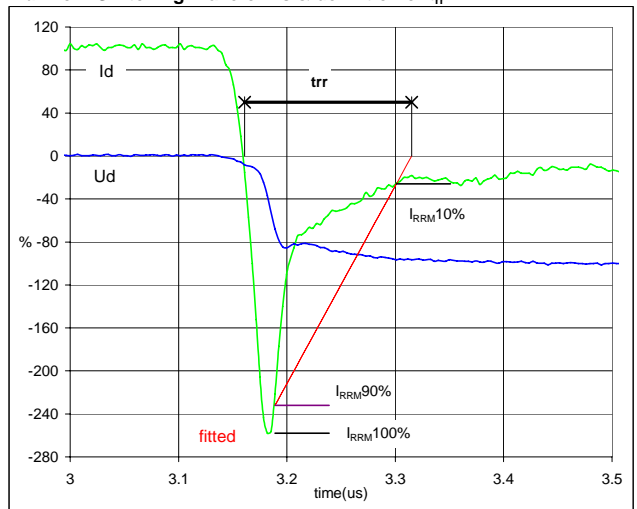
Gate voltage vs Gate charge (measured)



$V_{GEoff} = -15$ V
 $V_{GEon} = 15$ V
 $V_C(100\%) = 600$ V
 $I_C(100\%) = 25$ A
 $Q_g = 1175.08$ nC

Figure 8 Output inverter IGBT

Turn-off Switching Waveforms & definition of t_{rr}

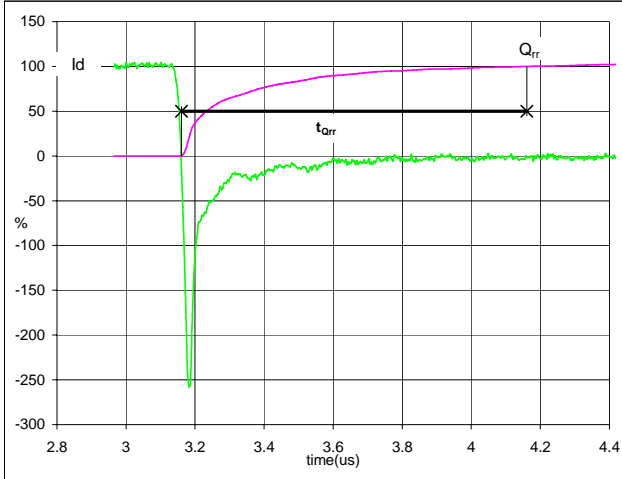


$V_d(100\%) = 600$ V
 $I_d(100\%) = 25$ A
 $I_{RRM}(100\%) = -65$ A
 $t_{rr} = 0.15$ μ s

Switching Definitions Output Inverter

Figure 9 Output inverter FRED

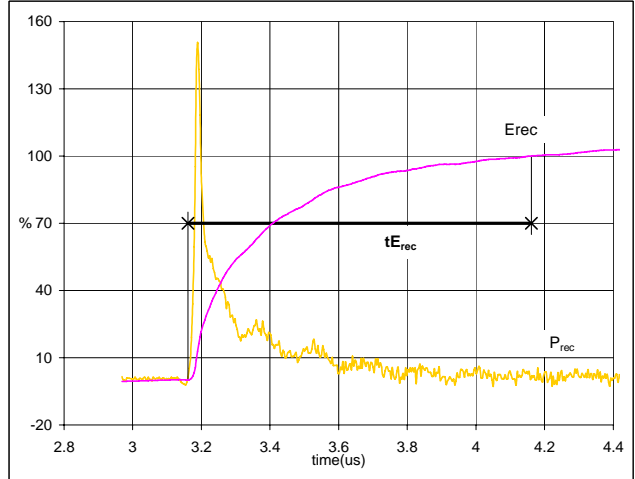
Turn-on Switching Waveforms & definition of t_{Qrr}
(t_{Qrr} = integrating time for Q_{rr})



I_d (100%) =	25	A
Q_{rr} (100%) =	4.64	μC
t_{Qrr} =	1.00	μs

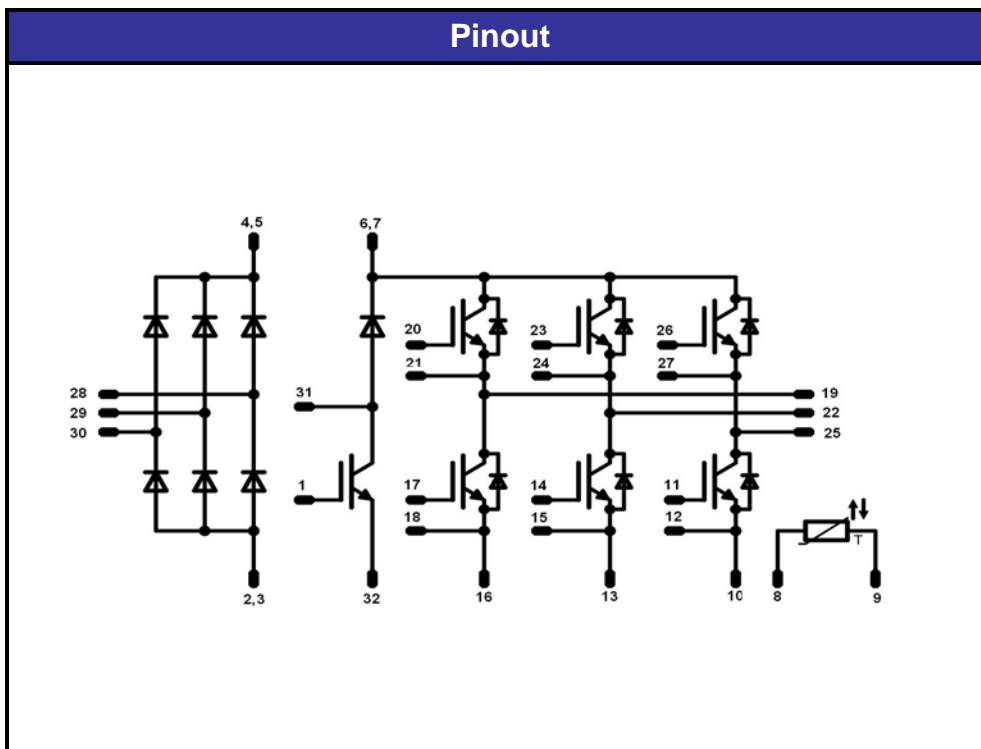
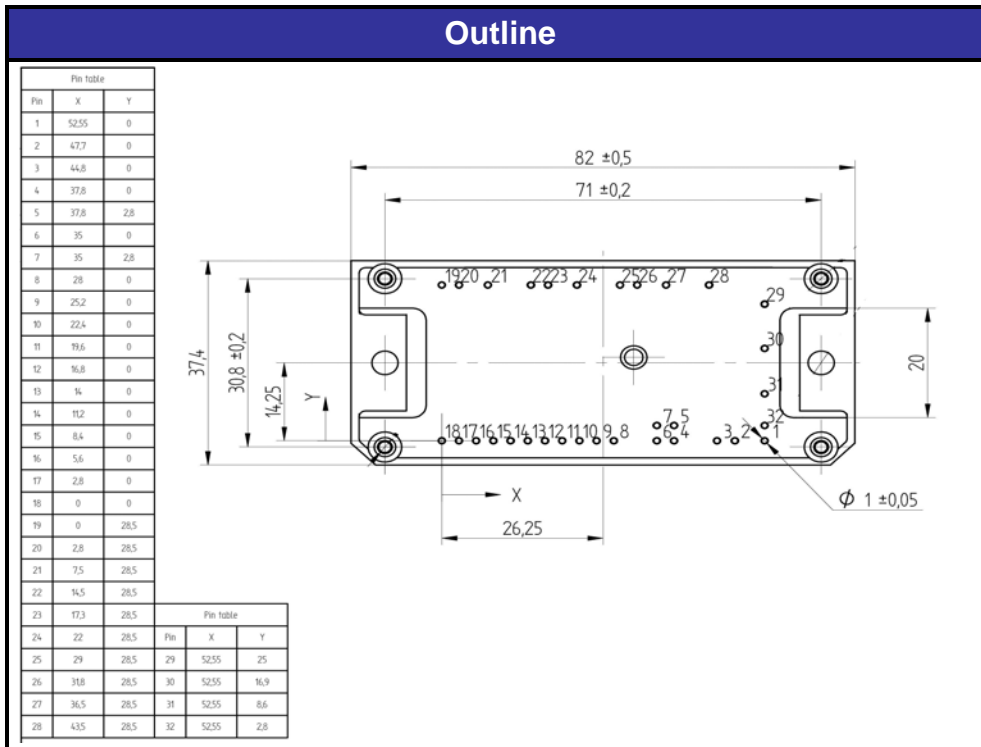
Figure 10 Output inverter FRED

Turn-on Switching Waveforms & definition of $t_{E_{rec}}$
($t_{E_{rec}}$ = integrating time for E_{rec})



P_{rec} (100%) =	14.95	kW
E_{rec} (100%) =	2.14	mJ
$t_{E_{rec}}$ =	1.00	μs

Package Outline and Pinout



PRODUCT STATUS DEFINITIONS

Datasheet Status	Product Status	Definition
Target	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice. The data contained is exclusively intended for technically trained staff.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data may be published at a later date. Vincotech reserves the right to make changes at any time without notice in order to improve design. The data contained is exclusively intended for technically trained staff.
Final	Full Production	This datasheet contains final specifications. Vincotech reserves the right to make changes at any time without notice in order to improve design. The data contained is exclusively intended for technically trained staff.

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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.